ABSTRACT OF THE DISCLOSURE

There is provided a method of making plurality of features in a first layer. A photoresist layer is formed over the first layer. Dense regions in the photoresist layer are exposed through a first mask under a first set of illumination conditions. Isolated regions in the photoresist layer are exposed through a second mask different from the first mask under a second set of illumination conditions different from the first set of illumination conditions. The exposed photoresist layer is patterned and then the first layer is patterned using the patterned photoresist layer as a mask.

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